SKiiP 21 NEB 06 - SKiiP 21 NEB 06 I

Absolute Maximum Ratings			
Symbol	**Conditions** [1]	**Values**	**Units**
Inverter & Chopper			
V_{CES}		600	V
V_{GES}		± 20	V
I_C	$T_{heatsink}$ = 25 / 80 °C	20 / 14	A
I_{CM}	t_p < 1 ms; $T_{heatsink}$ = 25 / 80 °C	40 / 28	A
$I_F = -I_C$	$T_{heatsink}$ = 25 / 80 °C	25 / 15	A
$I_{FM} = -I_{CM}$	t_p < 1 ms; $T_{heatsink}$ = 25 / 80 °C	50 / 30	A
Bridge Rectifier			
V_{RRM}		800	V
I_D	$T_{heatsink}$ = 80 °C	25	A
I_{FSM}	t_p = 10 ms; sin. 180 °, T_j = 25 °C	370	A
I^2t	t_p = 10 ms; sin. 180 °, T_j = 25 °C	680	A^2s
T_j		– 55 . . . + 150	°C
T_{stg}		– 55 . . . + 125	°C
V_{isol}	AC, 1 min.	2500	V

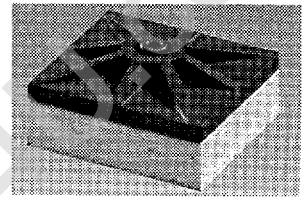
Characteristics					
Symbol	**Conditions** [1]	**min.**	**typ.**	**max.**	**Units**
IGBT - Inverter & Chopper					
V_{CEsat}	I_C = 20 A T_j = 25 (125) °C	–	2,1(2,2)	2,7(2,8)	V
$t_{d(on)}$	V_{CC} = 300 V; V_{GE} = 15 V	–	40	80	ns
t_r	I_C = 20 A; T_j = 125 °C	–	70	140	ns
$t_{d(off)}$	$R_{gon} = R_{goff}$ = 47 Ω	–	250	370	ns
t_f	inductive load	–	500	750	ns
$E_{on} + E_{off}$		–	2,5	–	mJ
C_{ies}	V_{CE} = 25 V; V_{GE} = 0 V, 1 MHz	–	1,1	–	nF
R_{thjh}	per IGBT	–	–	2,5	K/W
Diode [2] - Inverter & Chopper					
$V_F = V_{EC}$	I_F = 25 A T_j = 25 (125) °C	–	1,45(1,4)	1,7(1,7)	V
V_{TO}	T_j = 125 °C	–	0,85	0,9	V
r_T	T_j = 125 °C	–	22	32	mΩ
I_{RRM}	I_F = 25 A, V_R = – 300 V	–	25	–	A
Q_{rr}	di_F/dt = – 500 A/µs	–	2,5	–	µC
E_{off}	V_{GE} = 0 V, T_j = 125 °C	–	0,75	–	mJ
R_{thjh}	per diode	–	–	2,6	K/W
Diode - Rectifier					
V_F	I_F = 25 A, T_j = 25 °C	–	1,2	–	V
R_{thjh}	per diode	–	–	2,6	K/W
Temperature Sensor					
R_{TS}	T = 25 / 100 °C		1000 / 1670		Ω
Shunts (SKiiP 21 NEB 06 I)					
$R_{cs(dc)}$	5 %		10		mΩ
$R_{cs(ac)}$	1 %		10		mΩ
Mechanical Data					
M1	case to heatsink, SI Units	2,5	–	3,5	Nm
Case			M2		

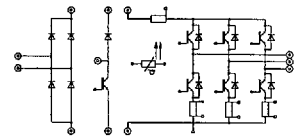
MiniSKiiP 2
SEMIKRON integrated intelligent Power
SKiiP 21 NEB 06
SKiiP 21 NEB 06 I [3]

1-phase bridge rectifier + braking chopper + 3-phase bridge inverter

Preliminary Data

Case M2





Features

- High level power integration
- One-screw-mounting to the customer heatsink, compact design
- Low thermal impedance due to durable ceramic insulation
- Pressure contact technology with simple connection to DCB through pressure contact (no soldering) and with increased power cycling capability
- Low stray inductance
- High power density, low losses
- Integrated temperature sensor
- Integrated shunts for dc and ac current (SKiiP 21 NEB 06 I)
- Mechanical drawing available on disc for Auto CAD 12 (.DWG, .DXF)

[1] $T_{heatsink}$ = 25 °C, unless otherwise specified
[2] CAL = Controlled Axial Lifetime Technology (soft and fast recovery)
[3] With integrated shunts for dc and ac current

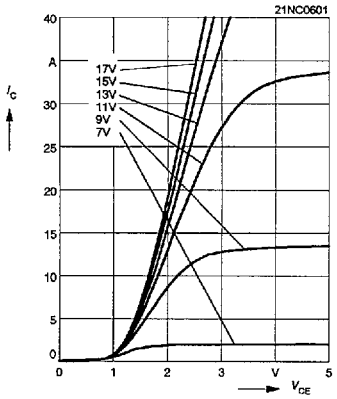


Fig. 1 Typ. output characteristic, t_p = 80 µs; 25 °C

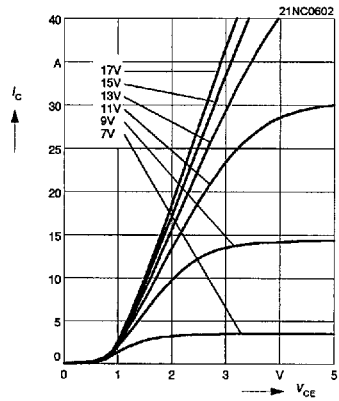
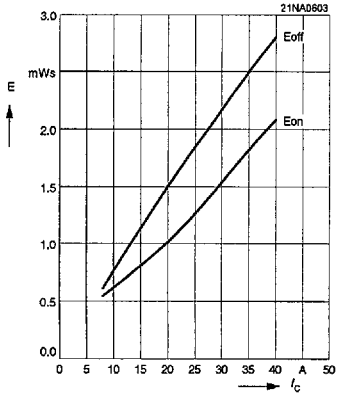
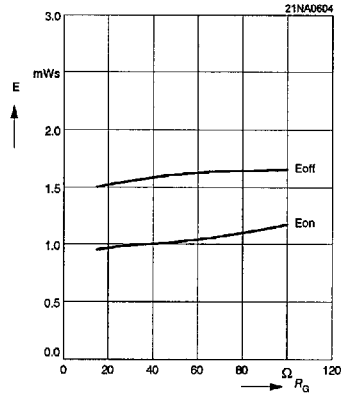


Fig. 2 Typ. output characteristic, t_p = 80 µs; 125 °C



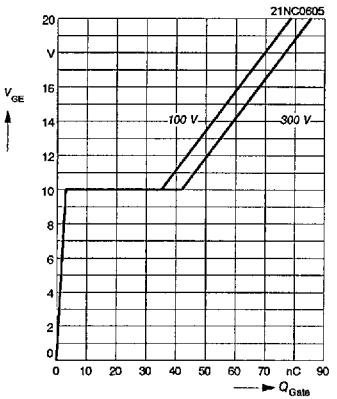
T_j = 125 °C
V_{CE} = 300 V
V_{GE} = ± 15 V
R_G = 47 Ω

Fig. 3 Turn-on /-off energy = f (I_C)



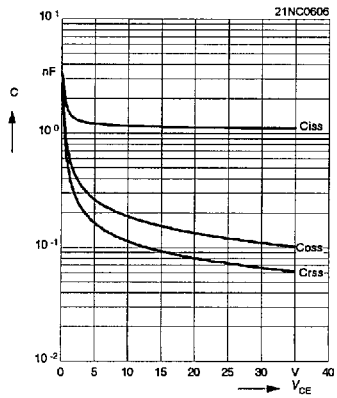
T_j = 125 °C
V_{CE} = 300 V
V_{GE} = ± 15 V
I_C = 20 A

Fig. 4 Turn-on /-off energy = f (R_G)



I_{Cpuls} = 20 A

Fig. 5 Typ. gate charge characteristic



V_{GE} = 0 V
f = 1 MHz

Fig. 6 Typ. capacitances vs. V_{CE}